



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

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Amdt
SDavis
7/1/03

Applicant: Craig T. Salling et al. Art Unit: 2815
Serial No.: 10/051,639 ✓ Examiner: Matthew C. Landau
Filed: 01/18/02 ✓ Docket: TI-32536
For: "ESD IMPROVEMENT BY A VERTICAL BIPOLAR TRANSISTOR WITH
LOW BREAKDOWN VOLTAGE AND HIGH BETA" ✓

June 26, 2003

Commissioner for Patents
P.O. Box 1450
Arlington, VA 22313-1450

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Ginger Cox
Ginger Cox

AMENDMENT PURSUANT TO 37 C.F.R. 1.115

Sir:

Responsive to the Office Action of March 27, 2003, please amend the application as follows:

IN THE CLAIMS

Cancel claims 8 and 19.

Amend claim 1 as follows:

1. An integrated circuit fabricated in ^{anterior} the surface of a semiconductor material of a first conductivity type, said circuit having [at the surface] at least one vertical bipolar transistor surrounded at least in part by a dielectric isolation zone, said transistor comprising:
[a first surface] an emitter region of opposite conductivity type[, suitable as an emitter];

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